MC33272A, MC33274A, NCV33272A, NCV33274A

Operational Amplifiers, Single Supply, High Slew Rate, Low Input Offset Voltage

The MC33272/74 series of monolithic operational amplifiers are quality fabricated with innovative Bipolar design concepts. This dual and quad operational amplifier series incorporates Bipolar inputs along with a patented Zip−R−Trim element for input offset voltage reduction. The MC33272/74 series of operational amplifiers exhibits low input offset voltage and high gain bandwidth product. Dual −doublet frequency compensation is used to increase the slew rate while maintaining low input noise characteristics. Its all NPN output stage exhibits no deadband crossover distortion, large output voltage swing, and an excellent phase and gain margin. It also provides a low open loop high frequency output impedance with symmetrical source and sink AC frequency performance.

Features

- Input Offset Voltage Trimmed to 100 μV (Typ)
- Low Input Bias Current: 300 nA
- Low Input Offset Current: 3.0 nA
- High Input Resistance: 16 MΩ
- Low Noise: 18 nV/$\sqrt{\text{Hz}}$ @ 1.0 kHz
- High Gain Bandwidth Product: 24 MHz @ 100 kHz
- High Slew Rate: 10 V/μs
- Power Bandwidth: 160 kHz
- Excellent Frequency Stability
- Unity Gain Stable: w/Capacitance Loads to 500 pF
- Large Output Voltage Swing: +14.1 V/ −14.6 V
- Low Total Harmonic Distortion: 0.003%
- Power Supply Drain Current: 2.15 mA per Amplifier
- Single or Split Supply Operation: +3.0 V to +36 V or ±1.5 V to ±18 V
- ESD Diodes Provide Added Protection to the Inputs
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
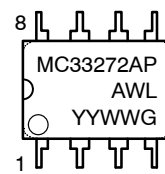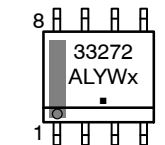- Pb−Free Packages are Available

ON Semiconductor®

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MARKING DIAGRAMS

DUAL
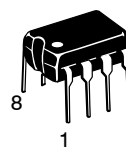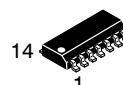
PDIP−8
P SUFFIX
CASE 626

MC33272AP
AWL
YYWWG

SOIC−8
D SUFFIX
CASE 751

33272
ALYWx

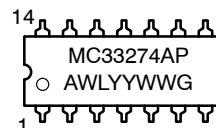x = A for MC33272AD/DR2
  = N for NCV33272ADR2

QUAD
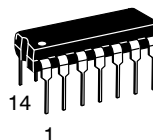
PDIP−14
P SUFFIX
CASE 646

MC33274AP
AWLYYWWG

SOIC−14
D SUFFIX
CASE 751A

MC33274ADG
AWLYWW

NCV33274AG
AWLYWW
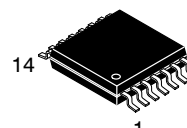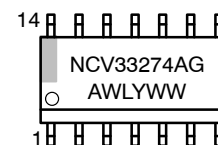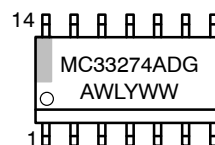
TSSOP−14
DTB SUFFIX
CASE 948G

MC33
274A
ALYW■

NCV3
3274A
ALYW■
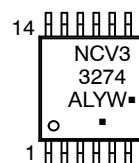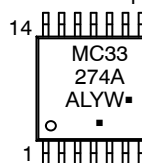
A   = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
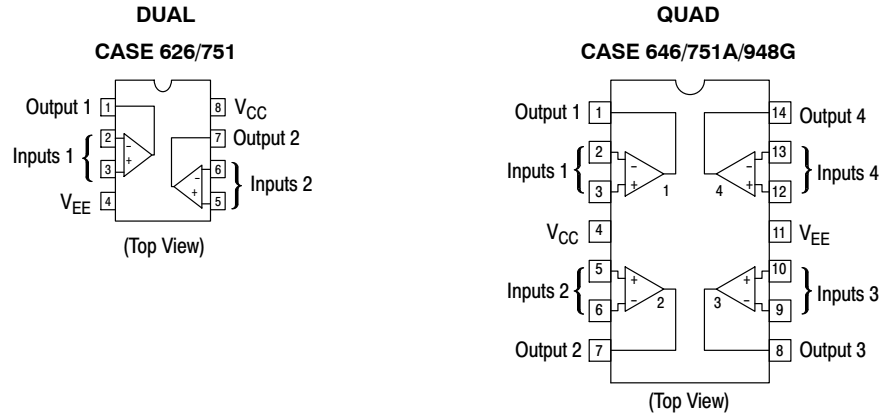WW, W = Work Week
G or ■ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

MC33272A, MC33274A, NCV33272A, NCV33274A

PIN CONNECTIONS

DUAL

CASE 626/751

Output 1 [1]   [8] V_{CC}
Inputs 1 { [2] [3] [7] Output 2
                    [6] } Inputs 2
V_{EE} [4]   [5]

(Top View)

QUAD

CASE 646/751A/948G

Output 1 [1]   [14] Output 4
Inputs 1 { [2] [3] 1   4   [13] [12] } Inputs 4
V_{CC} [4]   [11] V_{EE}
Inputs 2 { [5] [6] 2   3   [10] [9] } Inputs 3
Output 2 [7]   [8] Output 3

(Top View)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V_{CC} to V_{EE}	+36	V
Input Differential Voltage Range	V_{IDR}	Note 1	V
Input Voltage Range	V_{IR}	Note 1	V
Output Short Circuit Duration (Note 2)	t_{SC}	Indefinite	sec
Maximum Junction Temperature	T_J	+150	°C
Storage Temperature	T_{stg}	−60 to +150	°C
ESD Protection at Any Pin – Human Body Model – Machine Model	V_{esd}	2000 200	V
Maximum Power Dissipation	P_D	Note 2	mW
Operating Temperature Range MC33272A, MC33274A NCV33272A, NCV33274A	T_A	−40 to +85 −40 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. Either or both input voltages should not exceed V_{CC} or V_{EE}.
2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded (see Figure 2).

DC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = −15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Typ	Max	Unit

Input Offset Voltage (R_S = 10 Ω, V_{CM} = 0 V, V_O = 0 V)
 (V_{CC} = +15 V, V_{EE} = −15 V)
     T_A = +25°C
     T_A = −40° to +85°C
     T_A = −40° to +125°C (NCV33272A)
     T_A = −40° to +125°C (NCV33274A)
 (V_{CC} = 5.0 V, V_{EE} = 0)
     T_A = +25°C
	3	$|V_{IO}|$	
			
			 −
			 −
			 −
			 −
			
			 −
				
				 0.1
				 −
				 −
				 −
				
				 −
					
					 1.0
					 1.8
					 2.5
					 3.5
					
					 2.0
						mV

Average Temperature Coefficient of Input Offset Voltage R_S = 10 Ω, V_{CM} = 0 V, V_O = 0 V, T_A = −40° to +125°C	3	$\Delta V_{IO}/\Delta T$	−	2.0	−	µV/°C

Input Bias Current (V_{CM} = 0 V, V_O = 0 V)
     T_A = +25°C
     T_A = T_{low} to T_{high}
	4, 5	I_{IB}	
			 −
			 −
				
				 300
				 −
					
					 650
					 800
						nA

Input Offset Current (V_{CM} = 0 V, V_O = 0 V)
     T_A = +25°C
     T_A = T_{low} to T_{high}
		$|I_{IO}|$	
			 −
			 −
				
				 3.0
				 −
					
					 65
					 80
						nA

Common Mode Input Voltage Range (ΔV_{IO} = 5.0 mV, V_O = 0 V) T_A = +25°C	6	V_{ICR}		V_{EE} to (V_{CC} −1.8)		V

Large Signal Voltage Gain (V_O = 0 V to 10 V, R_L = 2.0 kΩ)
     T_A = +25°C
     T_A = T_{low} to T_{high}
	7	A_{VOL}	
			 90
			 86
				
				 100
				 −
					
					 −
					 −
						dB

Output Voltage Swing (V_{ID} = ±1.0 V)
 (V_{CC} = +15 V, V_{EE} = −15 V)
     R_L = 2.0 kΩ
     R_L = 2.0 kΩ
     R_L = 10 kΩ
     R_L = 10 kΩ
 (V_{CC} = 5.0 V, V_{EE} = 0 V)
     R_L = 2.0 kΩ
     R_L = 2.0 kΩ
	8, 9, 12
	
	 10, 11
		
		 V_O+
		 V_O-
		 V_O+
		 V_O-
		
		 V_{OL}
		 V_{OH}
			
			 13.4
			 −
			 13.4
			 −
			
			 −
			 3.7
				
				 13.9
				 −13.9
				 14
				 −14.7
				
				 −
				 −
					
					 −
					 −13.5
					 −
					 −14.1
					
					 0.2
					 5.0
						V

Common Mode Rejection (V_{in} = +13.2 V to −15 V)	13	CMR	80	100	−	dB
Power Supply Rejection V_{CC}/V_{EE} = +15 V/ −15 V, +5.0 V/ −15 V, +15 V/ −5.0 V	14, 15	PSR	 80	 105	 −	dB

Output Short Circuit Current (V_{ID} = 1.0 V, Output to Ground)
     Source
     Sink
	16	I_{SC}	
			 +25
			 −25
				
				 +37
				 −37
					
					 −
					 −
						mA

Power Supply Current Per Amplifier (V_O = 0 V)
 (V_{CC} = +15 V, V_{EE} = −15 V)
     T_A = +25°C
     T_A = T_{low} to T_{high}
 (V_{CC} = 5.0 V, V_{EE} = 0 V)
     T_A = +25°C
	17	I_{CC}	
			
			 −
			 −
			
			 −
				
				 2.15
				 −
				
				 −
					
					 2.75
					 3.0
					
					 2.75
						mA

3. MC33272A, MC33274A T_{low} = −40°C T_{high} = +85°C
    NCV33272A, NCV33274A T_{low} = −40°C T_{high} = +125°C

AC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = −15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Typ	Max	Unit
Slew Rate (V_{in} = −10 V to +10 V, R_L = 2.0 kΩ, C_L = 100 pF, A_V = +1.0 V)	18, 33	SR	8.0	10	–	V/μs
Gain Bandwidth Product (f = 100 kHz)	19	GBW	17	24	–	MHz
AC Voltage Gain (R_L = 2.0 kΩ, V_O = 0 V, f = 20 kHz)	20, 21, 22	A_{VO}	–	65	–	dB
Unity Gain Bandwidth (Open Loop)		BW	–	5.5	–	MHz
Gain Margin (R_L = 2.0 kΩ, C_L = 0 pF)	23, 24, 26	A_m	–	12	–	dB
Phase Margin (R_L = 2.0 kΩ, C_L = 0 pF)	23, 25, 26	ϕ_m	–	55	–	Deg
Channel Separation (f = 20 Hz to 20 kHz)	27	CS	–	−120	–	dB
Power Bandwidth (V_O = 20 V_{pp}, R_L = 2.0 kΩ, THD ≤ 1.0%)		BW_P	–	160	–	kHz
Total Harmonic Distortion (R_L = 2.0 kΩ, f = 20 Hz to 20 kHz, V_O = 3.0 V_{rms}, A_V = +1.0)	28	THD	–	0.003	–	%
Open Loop Output Impedance (V_O = 0 V, f = 6.0 MHz)	29	$|Z_O|$	–	35	–	Ω
Differential Input Resistance (V_{CM} = 0 V)		R_{in}	–	16	–	MΩ
Differential Input Capacitance (V_{CM} = 0 V)		C_{in}	–	3.0	–	pF
Equivalent Input Noise Voltage (R_S = 100 Ω, f = 1.0 kHz)	30	e_n	–	18	–	nV/√Hz
Equivalent Input Noise Current (f = 1.0 kHz)	31	i_n	–	0.5	–	pA/√Hz
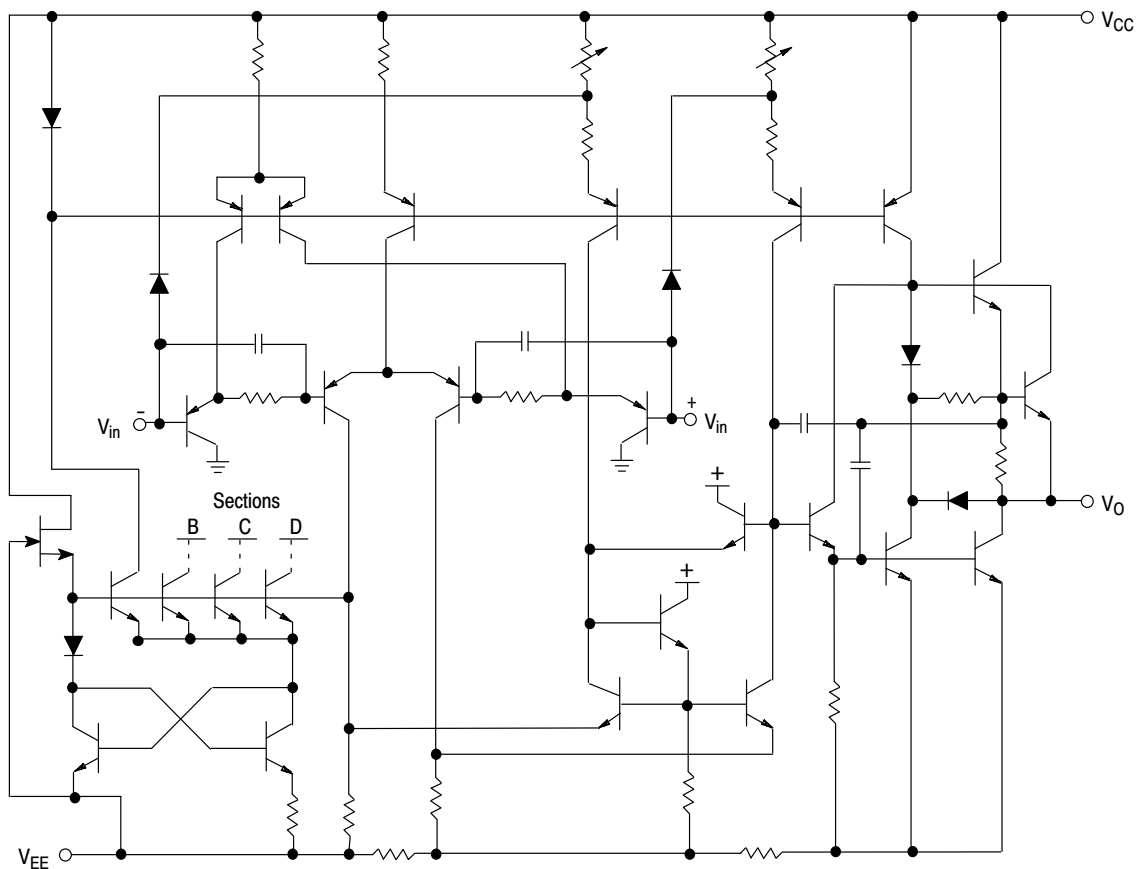
Figure 1. Equivalent Circuit Schematic
(Each Amplifier)
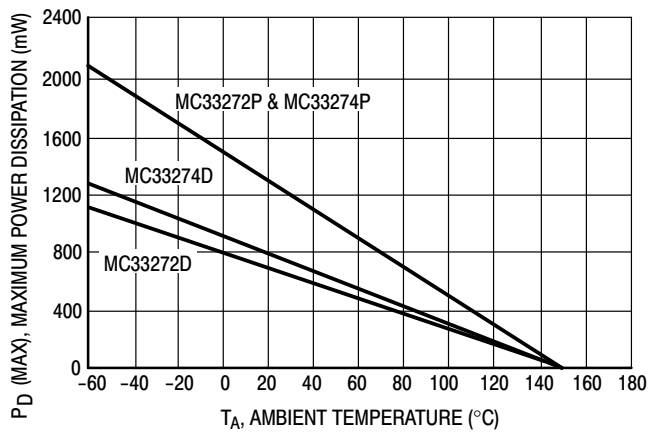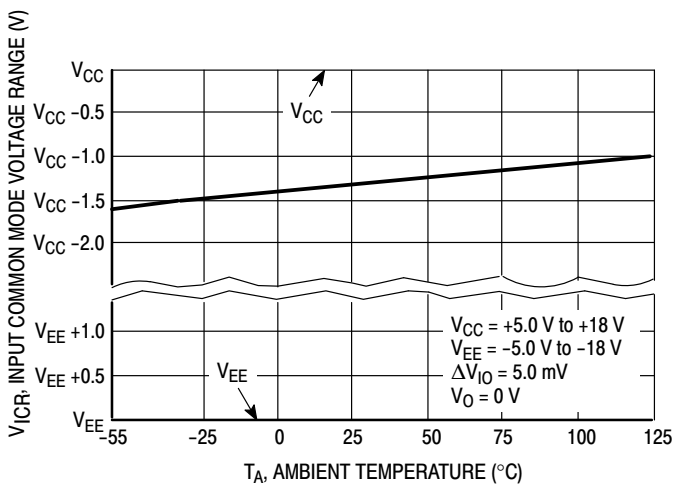
Figure 2. Maximum Power Dissipation
versus Temperature
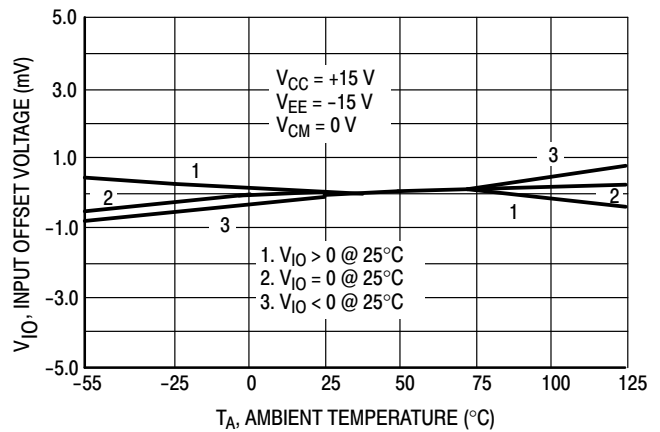
Figure 3. Input Offset Voltage versus
Temperature for Typical Units
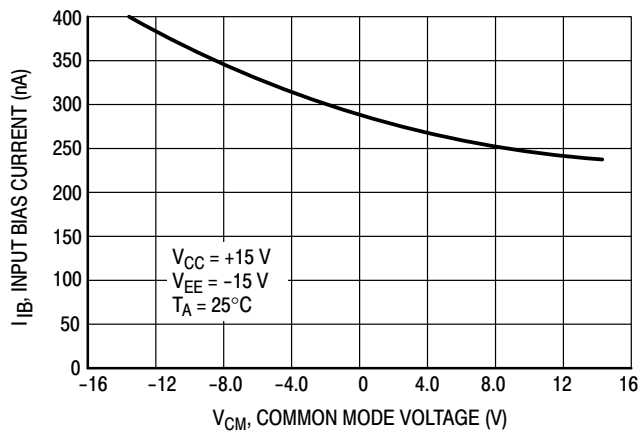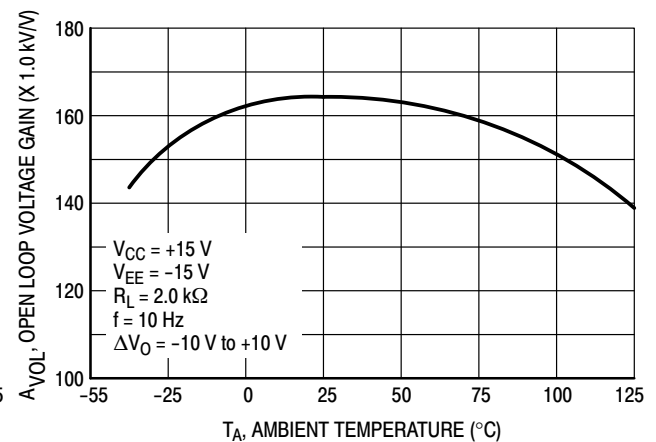

Figure 4. Input Bias Current versus
Common Mode Voltage
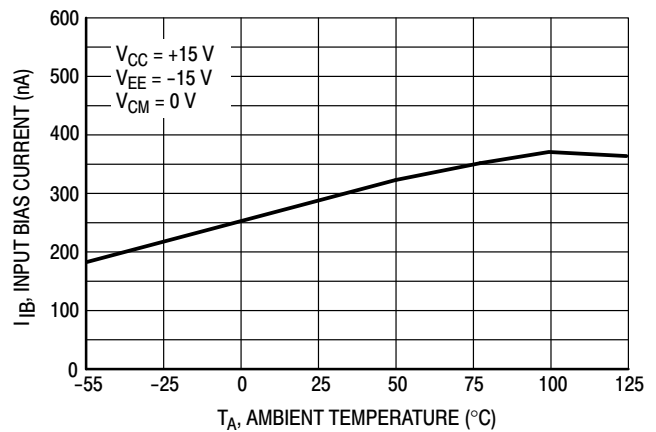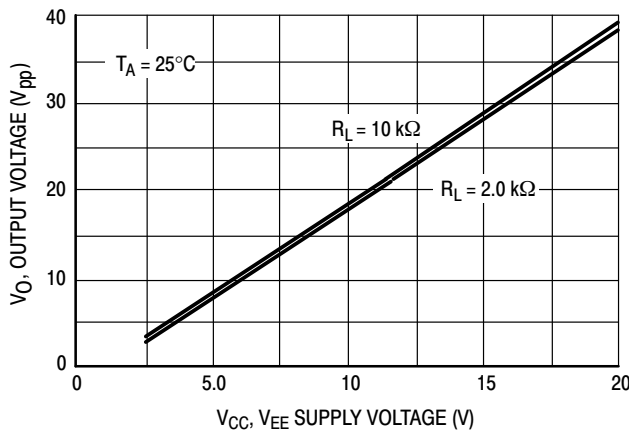

Figure 5. Input Bias Current
versus Temperature

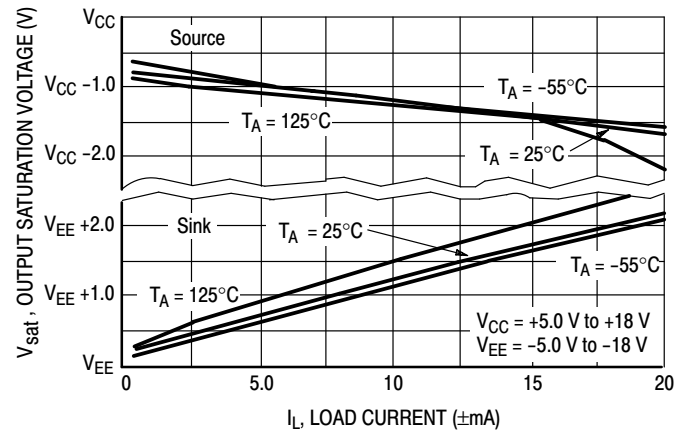Figure 6. Input Common Mode Voltage
Range versus Temperature
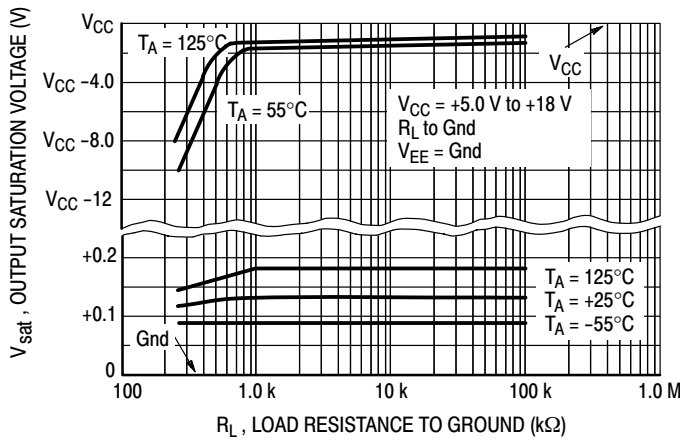

Figure 7. Open Loop Voltage Gain
versus Temperature

Figure 8. Split Supply Output Voltage Swing versus Supply Voltage

Figure 9. Split Supply Output Saturation Voltage versus Load Current

Figure 10. Single Supply Output Saturation Voltage versus Load Resistance to Ground
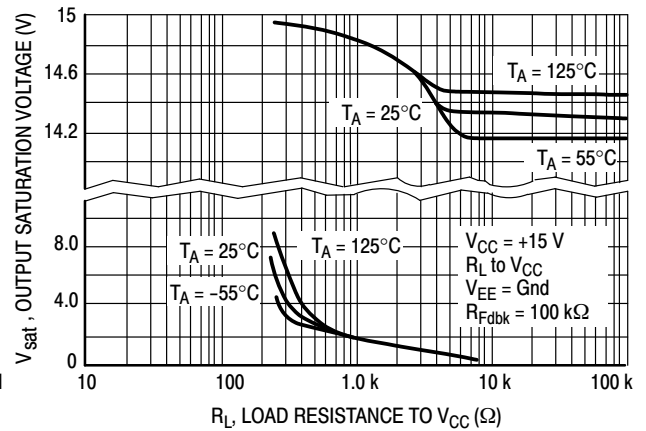
Figure 11. Single Supply Output Saturation Voltage versus Load Resistance to V_{CC}
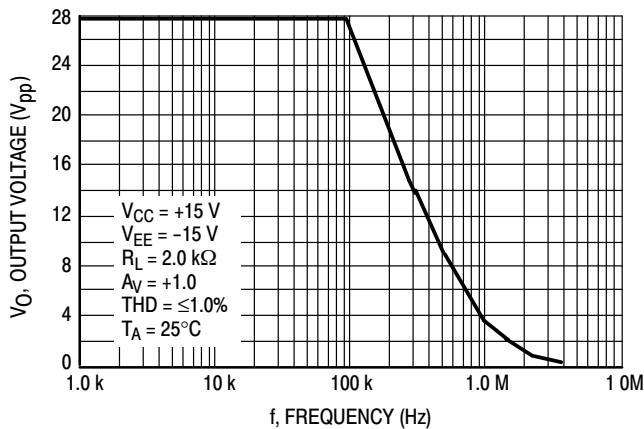
Figure 12. Output Voltage versus Frequency
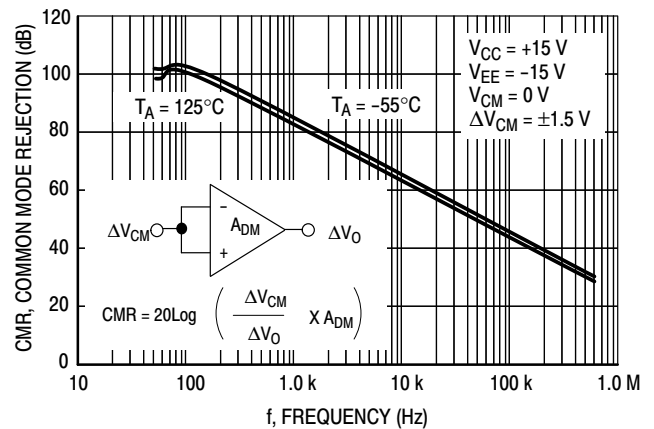
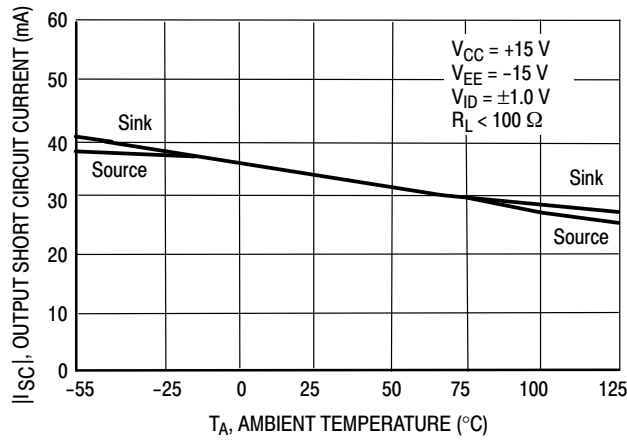**Figure 13. Common Mode Rejection versus Frequency**
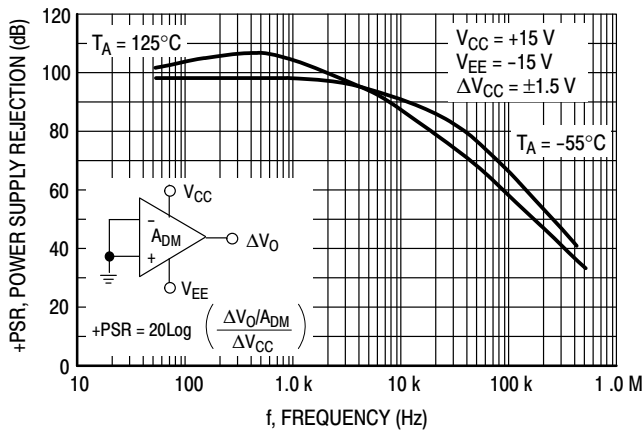
Figure 14. Positive Power Supply Rejection versus Frequency
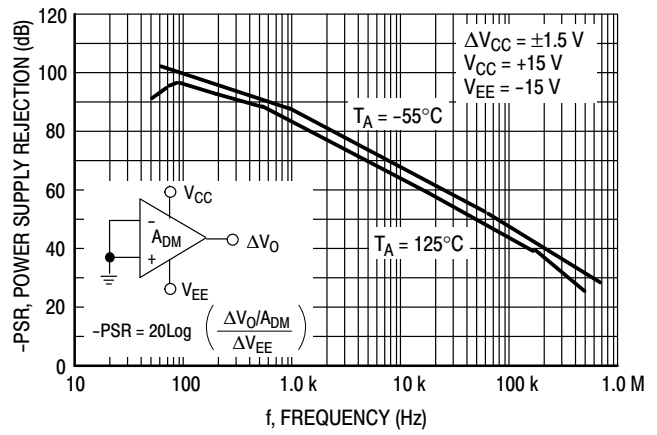
Figure 15. Negative Power Supply Rejection versus Frequency
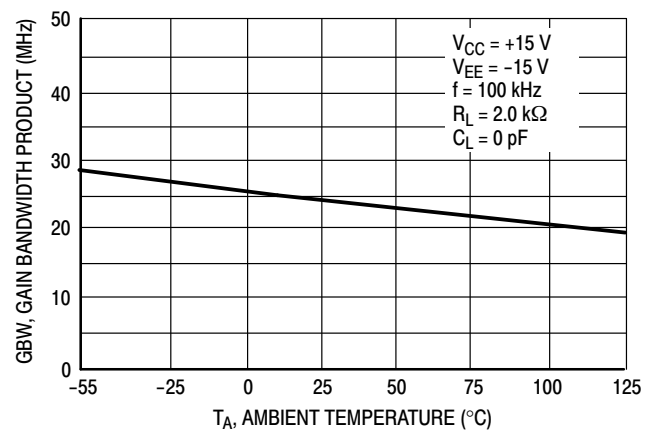

Figure 16. Output Short Circuit Current versus Temperature
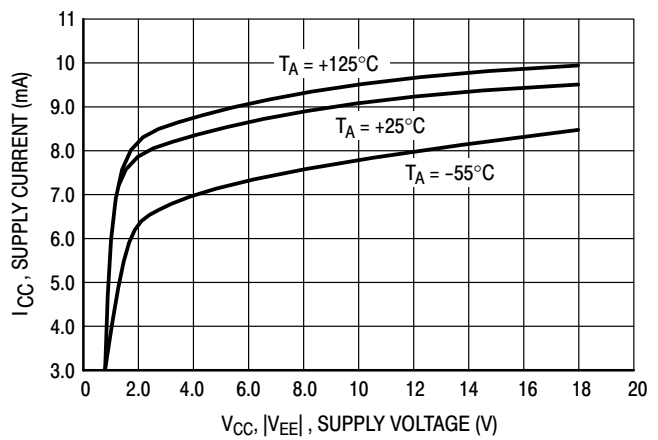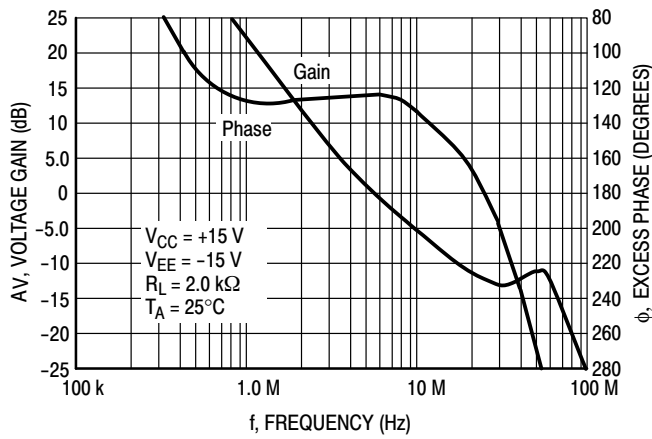

Figure 17. Supply Current versus Supply Voltage
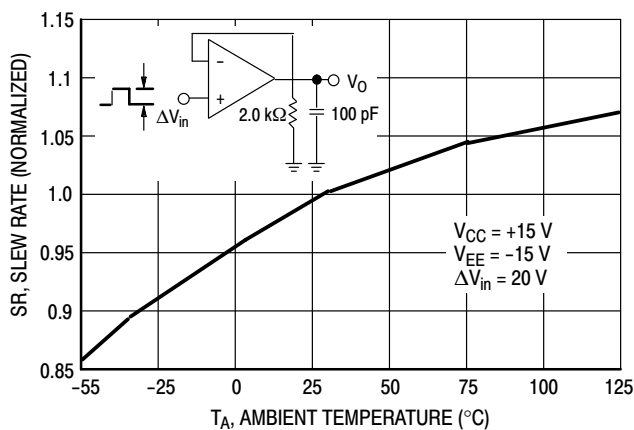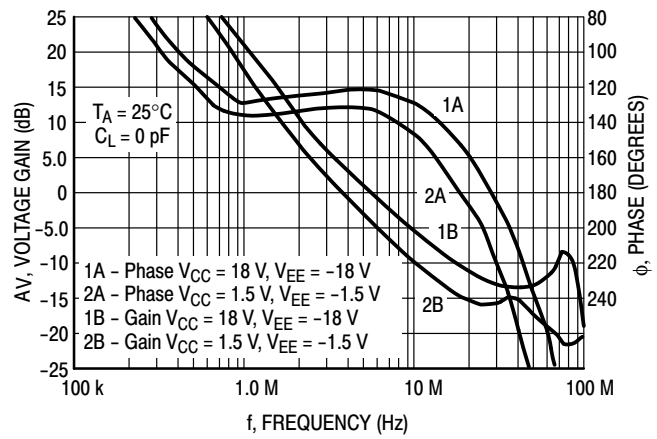

Figure 18. Normalized Slew Rate versus Temperature

Figure 19. Gain Bandwidth Product versus Temperature

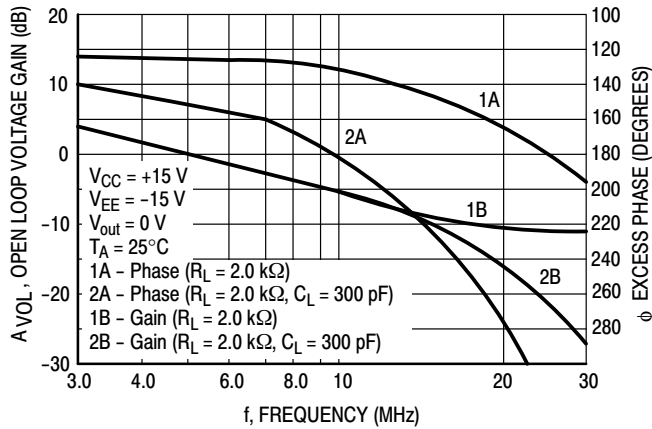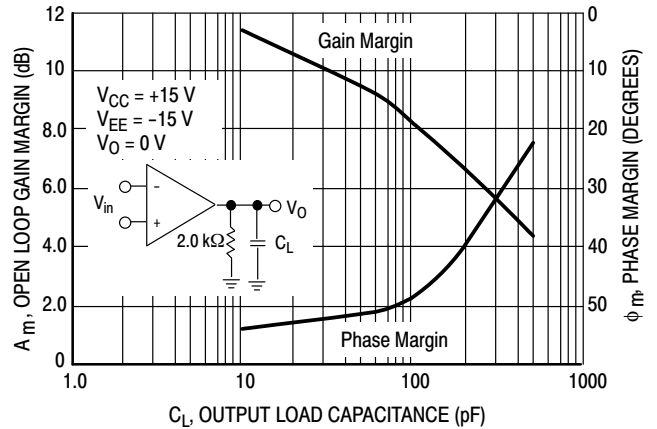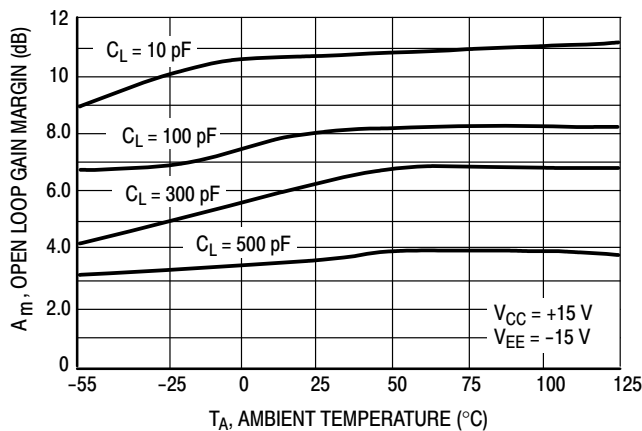Figure 20. Voltage Gain and Phase
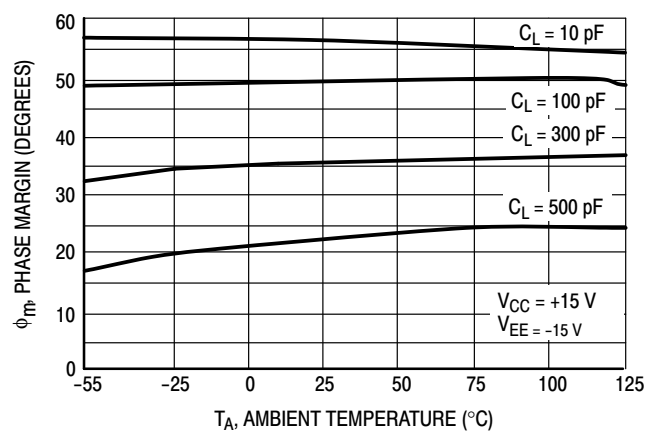versus Frequency

Figure 21. Gain and Phase
versus Frequency

Figure 22. Open Loop Voltage Gain and
Phase versus Frequency

Figure 23. Open Loop Gain Margin and Phase
Margin versus Output Load Capacitance

Figure 24. Open Loop Gain Margin
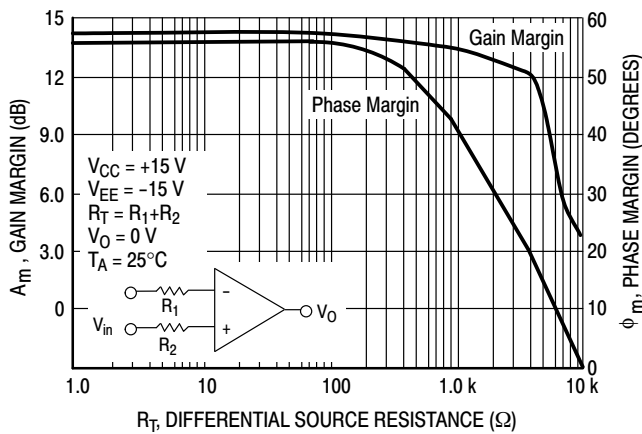versus Temperature

Figure 25. Phase Margin versus Temperature

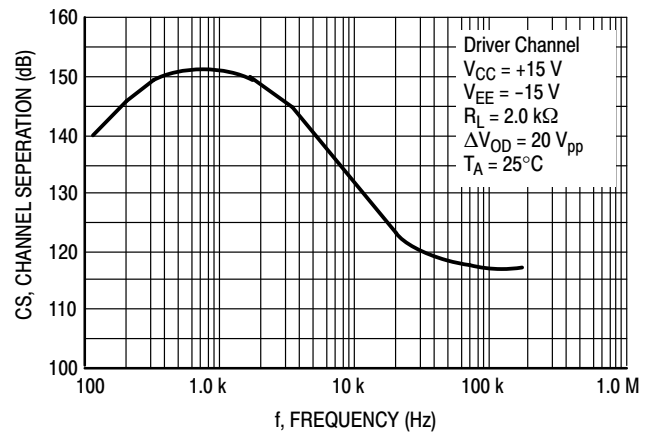**Figure 26. Phase Margin and Gain Margin versus Differential Source Resistance**

Figure 27. Channel Separation versus Frequency
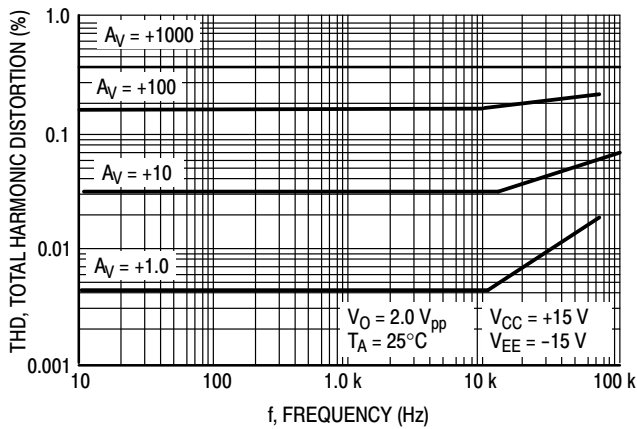

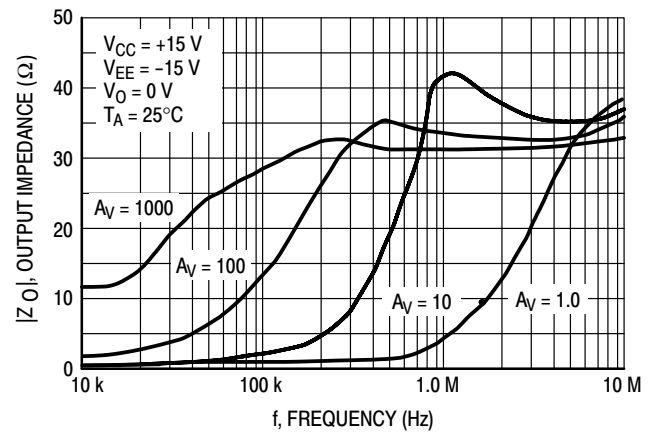**Figure 28. Total Harmonic Distortion versus Frequency**

Figure 29. Output Impedance versus Frequency

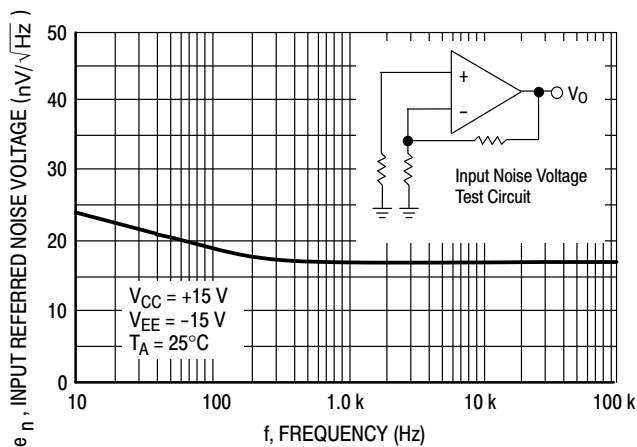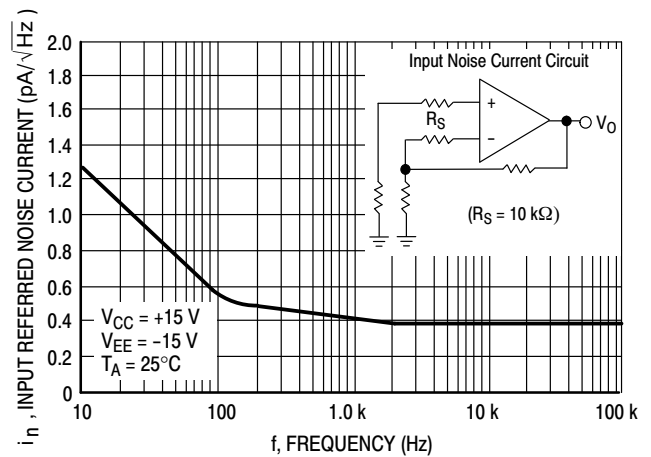**Figure 30. Input Referred Noise Voltage versus Frequency**

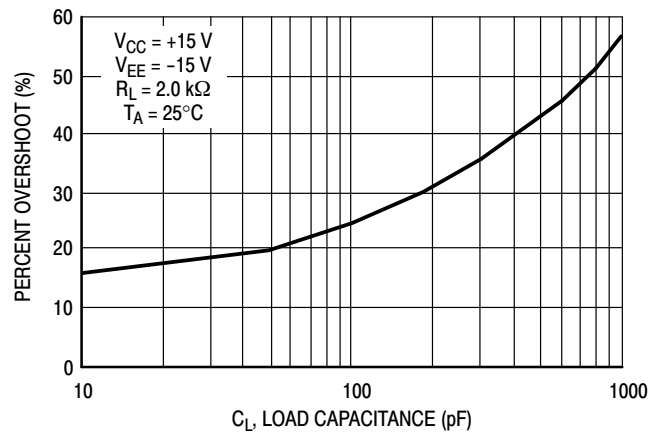**Figure 31. Input Referred Noise Current versus Frequency**

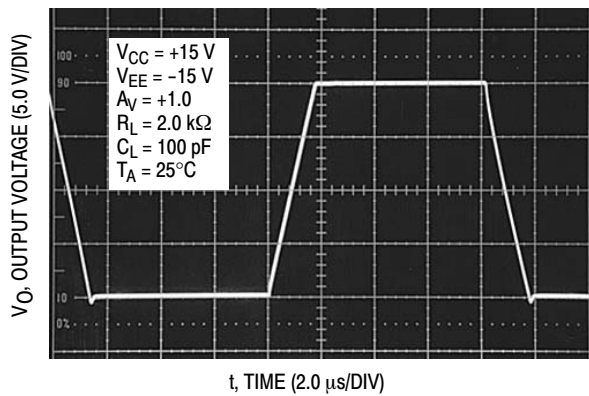Figure 32. Percent Overshoot versus
Load Capacitance

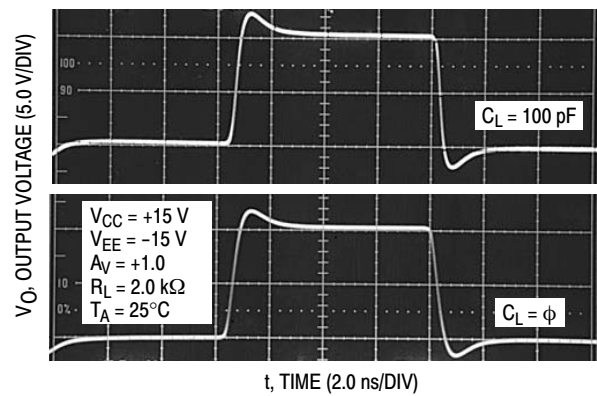Figure 33. Non-inverting Amplifier Slew Rate
for the MC33274

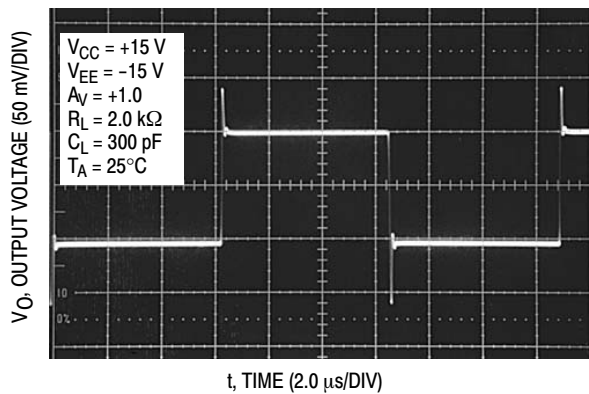Figure 34. Non-inverting Amplifier Overshoot
for the MC33274

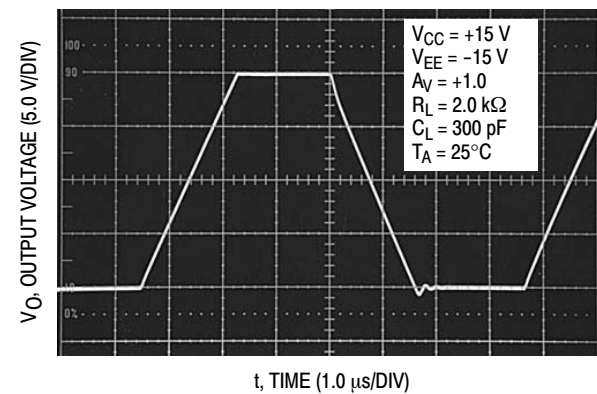Figure 35. Small Signal Transient Response
for MC33274

Figure 36. Large Signal Transient Response
for MC33274

ORDERING INFORMATION

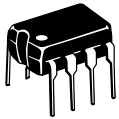| Device	Package	Shipping†
MC33272AD	SOIC−8	98 Units / Rail
MC33272ADG	SOIC−8 (Pb−Free)	
MC33272ADR2	SOIC−8	2500 / Tape & Reel
MC33272ADR2G	SOIC−8 (Pb−Free)	
MC33272AP	PDIP−8	50 Units / Rail
MC33272APG	PDIP−8 (Pb−Free)	
NCV33272ADR2*	SOIC−8	2500 / Tape & Reel
NCV33272ADR2G*	SOIC−8 (Pb−Free)	
MC33274AD	SOIC−14	55 Units / Rail
MC33274ADG	SOIC−14 (Pb−Free)	
MC33274ADR2	SOIC−14	2500 / Tape & Reel
MC33274ADR2G	SOIC−14 (Pb−Free)	
MC33274ADTBR2G	TSSOP−14 (Pb−Free)	
MC33274AP	PDIP−14	25 Units / Rail
MC33274APG	PDIP−14 (Pb−Free)	
NCV33274AD*	SOIC−14	55 Units / Rail
NCV33274ADG*	SOIC−14 (Pb−Free)	
NCV33274ADR2*	SOIC−14	2500 / Tape & Reel
NCV33274ADR2G*	SOIC−14 (Pb−Free)	
NCV33274ADTBR2G*	TSSOP−14 (Pb−Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.
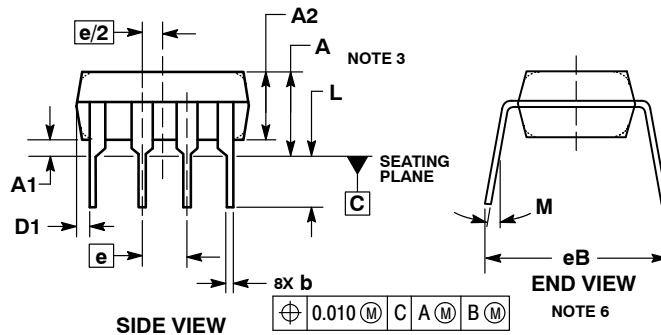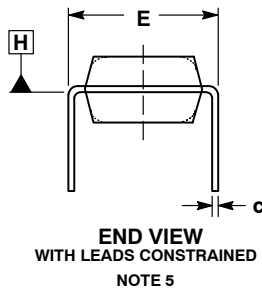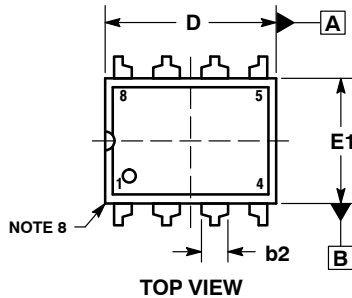
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

PDIP−8
CASE 626−05
ISSUE P

DATE 22 APR 2015

SCALE 1:1

TOP VIEW

END VIEW
WITH LEADS CONSTRAINED
NOTE 5

NOTE 8
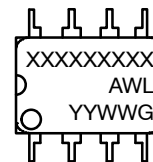
SIDE VIEW

8X b
⊕ 0.010 Ⓜ C A Ⓜ B Ⓜ

END VIEW
NOTE 6

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-AGE SEATED IN JEDEC SEATING PLANE GAUGE GS−3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	−−−−	0.210	−−−	5.33
A1	0.015	−−−−	0.38	−−−
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005	−−−−	0.13	−−−
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB	−−−−	0.430	−−−	10.92
L	0.115	0.150	2.92	3.81
M	−−−−	10°	−−−	10°

STYLE 1:
PIN 1. AC IN
     2. DC + IN
     3. DC − IN
     4. AC IN
     5. GROUND
     6. OUTPUT
     7. AUXILIARY
     8. V_{CC}

GENERIC
MARKING DIAGRAM*

XXXXXXXXX
AWL
YYWWG

XXXX = Specific Device Code
A   = Assembly Location
WL   = Wafer Lot
YY   = Year
WW   = Work Week
G   = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present.
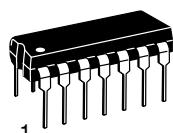
DOCUMENT NUMBER:	98ASB42420B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	PDIP−8		PAGE 1 OF 1

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PDIP−14
CASE 646−06
ISSUE S

DATE 22 APR 2015

SCALE 1:1

1

TOP VIEW

NOTE 8

END VIEW
WITH LEADS CONSTRAINED
NOTE 5

SIDE VIEW

⊕ 0.010 Ⓜ C A Ⓜ B Ⓜ

SEATING PLANE

END VIEW
NOTE 6

STYLES ON PAGE 2

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-AGE SEATED IN JEDEC SEATING PLANE GAUGE GS−3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	----	0.210	---	5.33
A1	0.015	----	0.38	---
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005	----	0.13	---
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB	----	0.430	---	10.92
L	0.115	0.150	2.92	3.81
M	----	10°	---	10°

GENERIC
MARKING DIAGRAM*

14

XXXXXXXXXXXX
XXXXXXXXXXXX
AWLYYWWG

1

XXXXX	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
YY	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

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DESCRIPTION:	PDIP−14		PAGE 1 OF 2

PDIP−14
CASE 646−06
ISSUE S

DATE 22 APR 2015

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. NO CONNECTION
5. GATE
6. SOURCE
7. DRAIN
8. DRAIN
9. SOURCE
10. GATE
11. NO CONNECTION
12. GATE
13. SOURCE
14. DRAIN

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. NO CONNECTION
5. SOURCE
6. DRAIN
7. GATE
8. GATE
9. DRAIN
10. SOURCE
11. NO CONNECTION
12. SOURCE
13. DRAIN
14. GATE

STYLE 6:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 7:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 8:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 9:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

STYLE 10:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 12:
PIN 1. COMMON CATHODE
2. COMMON ANODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. COMMON ANODE
7. COMMON CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. ANODE/CATHODE
14. ANODE/CATHODE

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DESCRIPTION:	PDIP−14	PAGE 2 OF 2

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SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

8
1
SCALE 1:1

−X−
A
8 5
B
S
1 4
−Y−
G

⊕ | 0.25 (0.010) Ⓜ | Y | Ⓜ |

C
SEATING PLANE
−Z−
◁ | 0.10 (0.004)
H
D

⊕ | 0.25 (0.010)Ⓜ | Z | Y Ⓢ | X Ⓢ |

N X 45°
K
M
J

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244
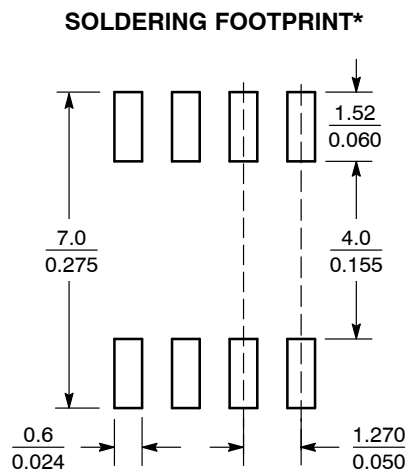
SOLDERING FOOTPRINT*

1.52 / 0.060

7.0 / 0.275

4.0 / 0.155

0.6 / 0.024

1.270 / 0.050

SCALE 6:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

8 XXXXX ALYWX 1
IC

8 XXXXX ALYWX 1
IC (Pb−Free)

8 XXXXXX AYWW 1
Discrete

8 XXXXXX AYWW 1
Discrete (Pb−Free)

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC−8 NB		PAGE 1 OF 2

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
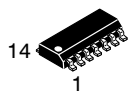6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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DESCRIPTION:	SOIC−8 NB		PAGE 2 OF 2

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SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

14

1

SCALE 1:1

D   A
   B

14   8

H   **E**

1   7

⊕ | 0.25 Ⓜ | B Ⓜ

13X **b**

⊕ | 0.25 Ⓜ | C | A Ⓢ | B Ⓢ

A3

L

DETAIL A

A

△ | 0.10

**e**   **A1**

C | SEATING PLANE

h
X 45°

DETAIL A

M

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

SOLDERING FOOTPRINT*

6.50

14X
1.18

1

1.27
PITCH

14X
0.58
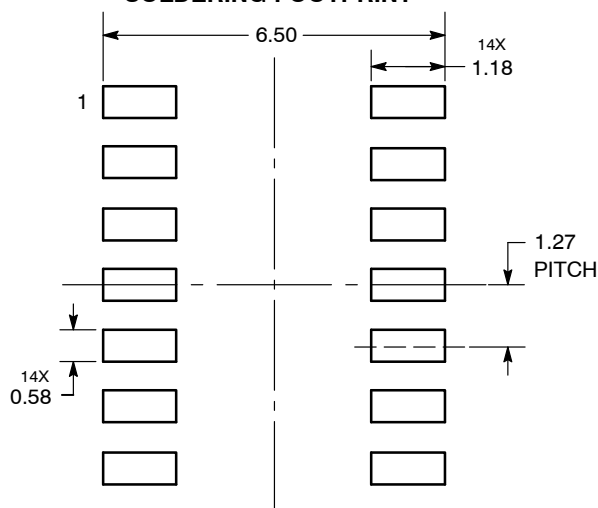
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

14

XXXXXXXXXG
AWLYWW

1
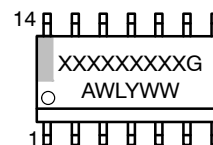
XXXXX	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC−14 NB		PAGE 1 OF 2

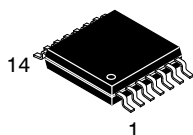© Semiconductor Components Industries, LLC, 2019

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STYLE 1:
PIN 1. COMMON CATHODE
    2. ANODE/CATHODE
    3. ANODE/CATHODE
    4. NO CONNECTION
    5. ANODE/CATHODE
    6. NO CONNECTION
    7. ANODE/CATHODE
    8. ANODE/CATHODE
    9. ANODE/CATHODE
  10. NO CONNECTION
  11. ANODE/CATHODE
  12. ANODE/CATHODE
  13. NO CONNECTION
  14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
    2. ANODE
    3. ANODE
    4. NO CONNECTION
    5. ANODE
    6. NO CONNECTION
    7. ANODE
    8. ANODE
    9. ANODE
  10. NO CONNECTION
  11. ANODE
  12. ANODE
  13. NO CONNECTION
  14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
    2. CATHODE
    3. CATHODE
    4. NO CONNECTION
    5. CATHODE
    6. NO CONNECTION
    7. CATHODE
    8. CATHODE
    9. CATHODE
  10. NO CONNECTION
  11. CATHODE
  12. CATHODE
  13. NO CONNECTION
  14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
    2. ANODE/CATHODE
    3. ANODE/CATHODE
    4. ANODE/CATHODE
    5. ANODE/CATHODE
    6. NO CONNECTION
    7. COMMON ANODE
    8. COMMON CATHODE
    9. ANODE/CATHODE
  10. ANODE/CATHODE
  11. ANODE/CATHODE
  12. ANODE/CATHODE
  13. NO CONNECTION
  14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
    2. CATHODE
    3. CATHODE
    4. CATHODE
    5. CATHODE
    6. CATHODE
    7. CATHODE
    8. ANODE
    9. ANODE
  10. ANODE
  11. ANODE
  12. ANODE
  13. ANODE
  14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
    2. COMMON ANODE
    3. COMMON CATHODE
    4. ANODE/CATHODE
    5. ANODE/CATHODE
    6. ANODE/CATHODE
    7. ANODE/CATHODE
    8. ANODE/CATHODE
    9. ANODE/CATHODE
  10. ANODE/CATHODE
  11. COMMON CATHODE
  12. COMMON ANODE
  13. ANODE/CATHODE
  14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
    2. ANODE/CATHODE
    3. ANODE/CATHODE
    4. NO CONNECTION
    5. ANODE/CATHODE
    6. ANODE/CATHODE
    7. COMMON ANODE
    8. COMMON ANODE
    9. ANODE/CATHODE
  10. ANODE/CATHODE
  11. NO CONNECTION
  12. ANODE/CATHODE
  13. ANODE/CATHODE
  14. COMMON CATHODE

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TSSOP−14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016

SCALE 2:1

14X **K** REF

⊕ | 0.10 (0.004) Ⓜ | T | U Ⓢ | V Ⓢ

△ | 0.15 (0.006) | T | U Ⓢ

2X **L/2**

L

PIN 1 IDENT.

△ | 0.15 (0.006) | T | U Ⓢ

A

−V−

B
−U−

N

0.25 (0.010)

M

N

F

DETAIL E

K

K1

J **J1**

SECTION N−N

C

△ | 0.10 (0.004)

−T− SEATING PLANE

D

G

H

DETAIL E

−W−

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*

14

XXXX
XXXX
ALYW▪

1
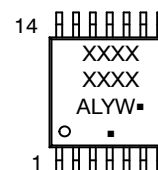
A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
▪	= Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT

7.06

1

0.65 PITCH

14X 0.36

14X 1.26

DIMENSIONS: MILLIMETERS
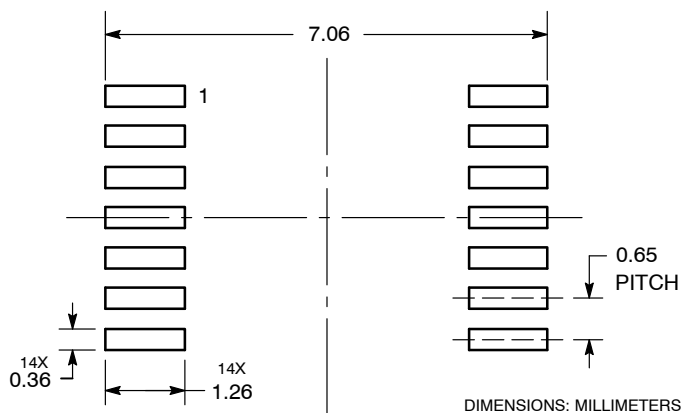
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PUBLICATION ORDERING INFORMATION

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